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(22)	2002 03 21		
(71)			
	575		
(72)			
	1 969-37		
	14 1102		
(74)			
	:		
(54)			

NOR

NOR

NOR

NOR

가

OR

가

PMOS

NOR

4

NOR

2

2

EL,

1

1

EL

2

1

EL

3

1

1

4 1 .

5a 5b 1 2 3 NOR

6 1 .

7 1 .

8 1 .

9a 9b .

10a 10b NAND PMOS NMOS

가

(organic electroluminescence, EL)

가 EL .

EL , N × M (IT

O), (Metal) 가 .

(EML, emission layer), (ETL, electron transport layer) (H

TL, hole transport layer) (EIL, electron injection layer)

r) (HIL, hole injection layer) .

(active matrix) (passive matrix) TFT

TFT ITO TFT

EL EL ,

EL ,

가 (ON) 가 , 가 ,

가 , 가 EL 가

9a , 1 PMOS 9b NMOS 4 NAND , CMOS

(static current)가 NAND PMOS NMOS

10a 10b 가 NAND PMOS NMOS

10a (Vout) (high) PMOS 가 , 10b GND NMOS 가

PMOS VDD 가 (Vout) (low) 가 .
 , PMOS NAND 가 , 4
 2 가 2
 가 .
 EL PMOS 가 , NAND PMOS NAND (PMOS 가 .
)
 가 가 가
 .
 가
 .
 가 , EL , EL 가 EL ,
 , 2 ,
 . NOR NAND .
 , 1 4 , 1 1
 , 2 1 2
 . 3 3 3 1 4
 , 3 1 3 4
 . 1 4
 .
 5
 , 5
 , 1 5
 1 5 NOR , NOR PMOS
 .
 1 5 NAND , NAND NMOS
 .

, n 가 1 가 2 가 . n 가 , n (n+1) 1
 2 n 가 . (n+1) 가 (n+1) n 1
 (n+1) 가 2 가 (n+1)
 , PMOS NAND NOR NMOS
 EL 가
 EL
 , 1 5 1 EL
 1 1 EL . 2 1
 EL
 1 (200) , 1 (300) EL EL (100),
 EL (100) (X₁, X₂, ..., X_M) (110) (Y₁, Y₂, ..., Y_N)
 (100) (X₁, X₂, ..., X_M) EL
 PMOS (110)
 (200) (X₁, X₂, ..., X_M) 가 , (300) (Y₁
 , Y₂, ..., Y_N) 가 .
 2 , 1 (200) 1 3 (210, 220,
 230) (240) .
 1 3 (210, 220, 230) , 1
 가
 80 240 1 3 (210, 220, 230)
 가 .
 (240) (VC1, VC2, VC3) 1 3 (21
 0, 220, 230) (RST1, RST2, RST3) 1 3 (210,
 220, 230) .
 , 3 5 1 .
 3 1 1 4 1 2
 3 NOR 5a 5b 1 6 1
 , 7 1 .

[illegible]

가 2 (220) (V_{out81}, V_{out82}, ..., V_{out160}) 2
(220) (VC2)가 (VC1, VC3)가 3 (23)
0) (V_{out161}, V_{out162}, ..., V_{out240}) 3 (230)
(VC3)가 (VC1, VC2)가 .

NOR 가 5a 5b (FF) PMOS 가
7 (buf) OR PMOS NOR
가

1 (210) 2 (220) 가 .
2 (210) (220) 1 (210) (V_{out80}) , 1
(VC1) (VC2) (VC1)가 1 (210)가
(RST2) 2 (220) (V_{out80}) 1 2 (220)
(VC2) (VC2) (RST2) 2 (220)
0) 2 가 (220) 3 (230) 가 1 2 (22

, 2 EL ,
2 EL 1 PMOS NMOS
, PMOS 1 (VC1, NO
VC2, VC3) R , NMOS 2 가
(VC1, VC2, VC3) NAND , 가

, (FF₁, FF₂, ..., FF_m) NOR (NOR1, NOR2, NOR3, NOR4) PMOS N
AND (NAND1, NAND2, NAND3, NAND4) NMOS (buf₁, buf₂
, ..., buf_m) OR AND , AND NAND

가 가
ST1, RST2, RST3) 1 2 가 , 1 3 (210, 220, 230) (R
가 가 가
가 .

가 ,

1.

, , ,

가 ,

,

NOR

NAND

2 ,

.

2.

1 ,

.

3.

1 ,

1

1

,

1

2

,

2

1

,

3

1

,

3

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3

,

3

1

4

4

.

4.

3 ,

,

1

4

.

5.

1 4 ,

5

6.

5 ,

5

7.

5 ,

1 5

8.

5 ,

1 5

NOR ,

NOR

PMOS

9.

7 ,

1 5

NAND ,

NAND

NMOS

10.

, ,

NAND

가 ,

NOR

가 , n
1 ,

1

가

1

가

2

가

n

(n+1)
(n+1)

n

2

가

2

,

(n+1)
가

3

가

n

1

11. 10 ,
2 (n+1) 2 가 (n+1) .
12. 10 11 ,
PMOS NOR .
13. 10 11 ,
NMOS NAND .
14. ,
가 ,
NOR NAND
2 ,
.
15. 14 ,
.
16. 14 ,
1 가 1 NOR ,
1 NOR 가 , 2 NOR 1 ,
3 1 NOR 가 ,
3 NOR ,
3 NOR 가 , 3 4 NOR
1 NOR 4 ,
5 NOR ,
1 5 NOR PMOS .

17.

16

1, 4 5 NOR

18.

14

1

가 1 NAND

1 NAND

2

가 ,

2 NAND

1

3

3 NAND

1 NAND

가 ,

3 NAND

1 NAND

4

가 ,

3
4 NAND

5 NAND

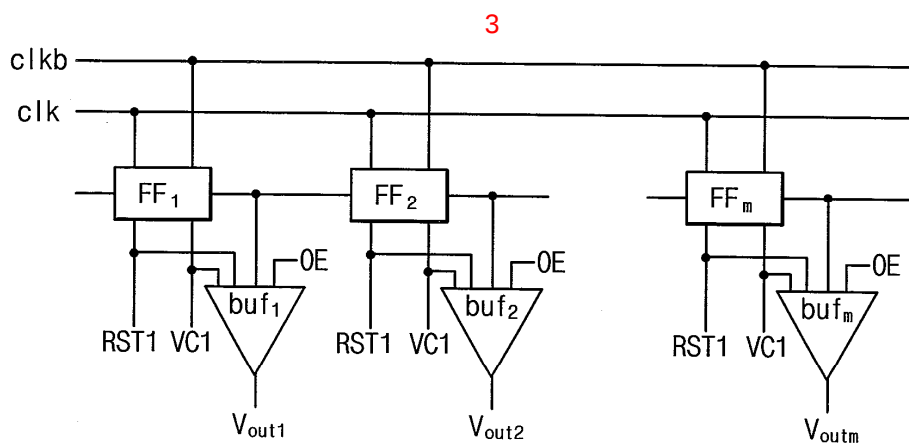
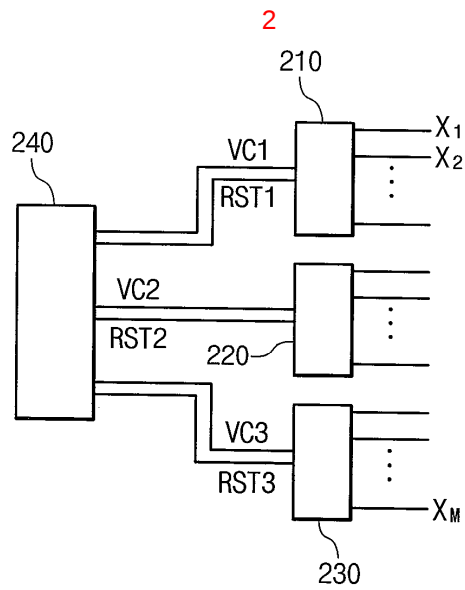
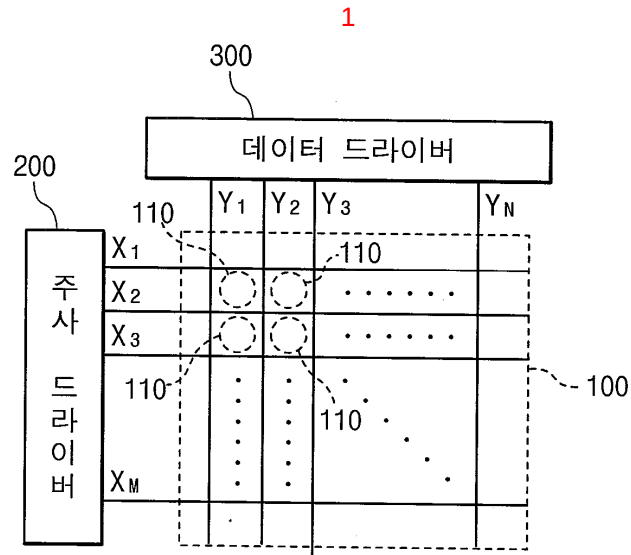
1 5 NAND

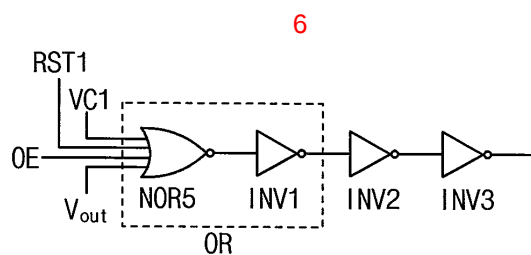
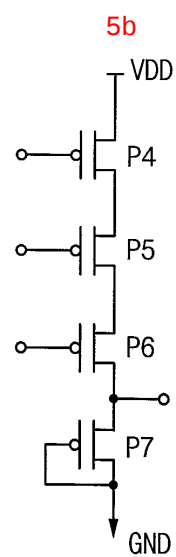
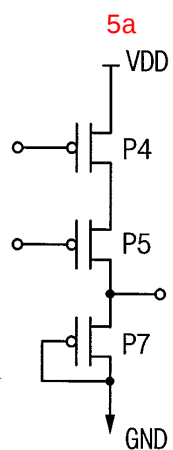
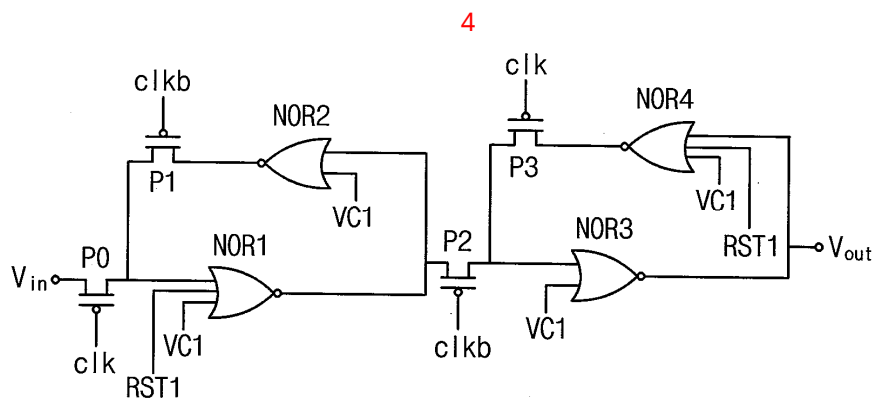
NMOS

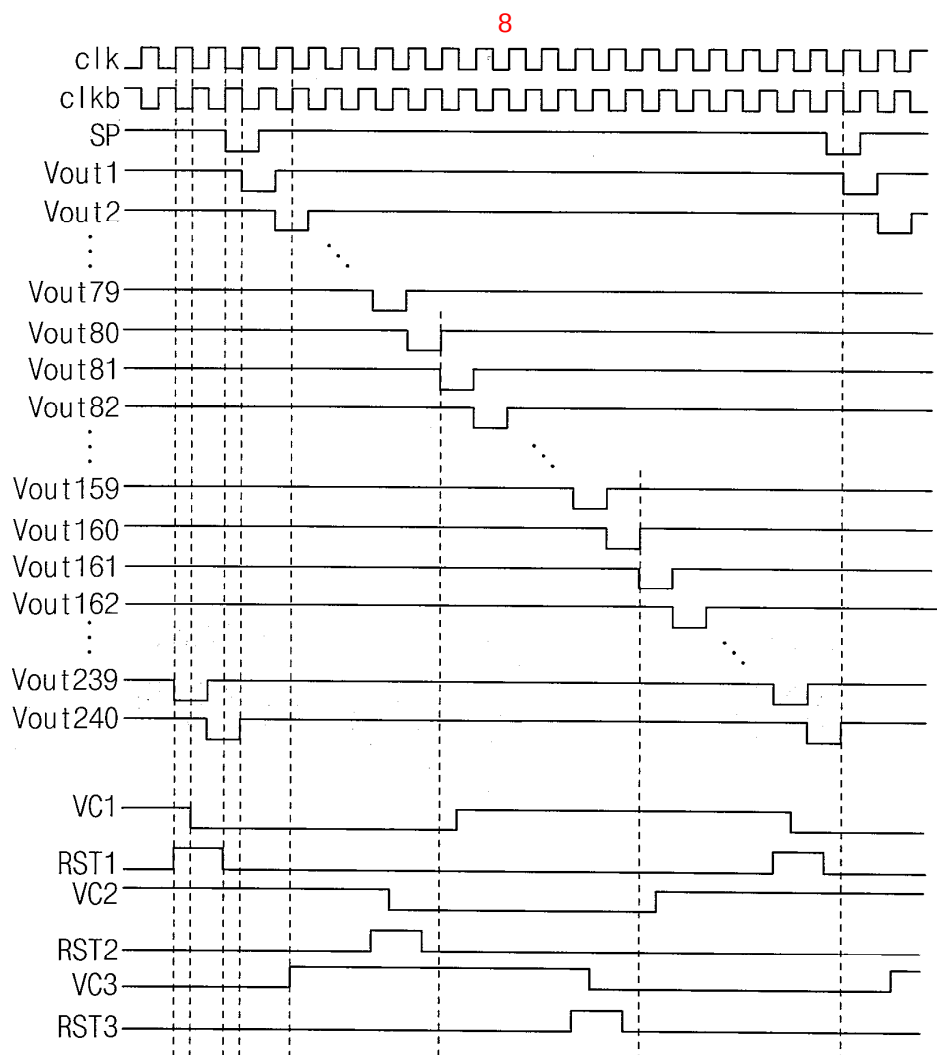
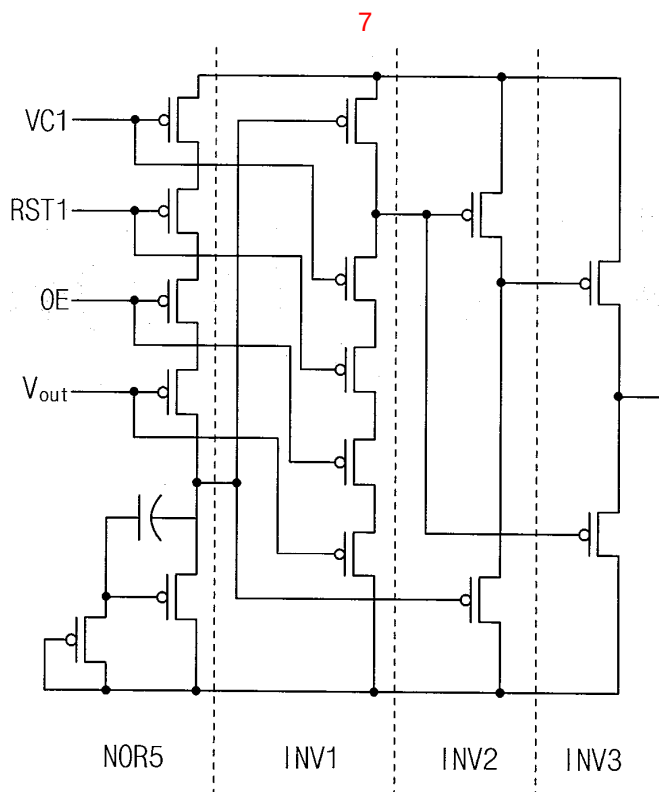
19.

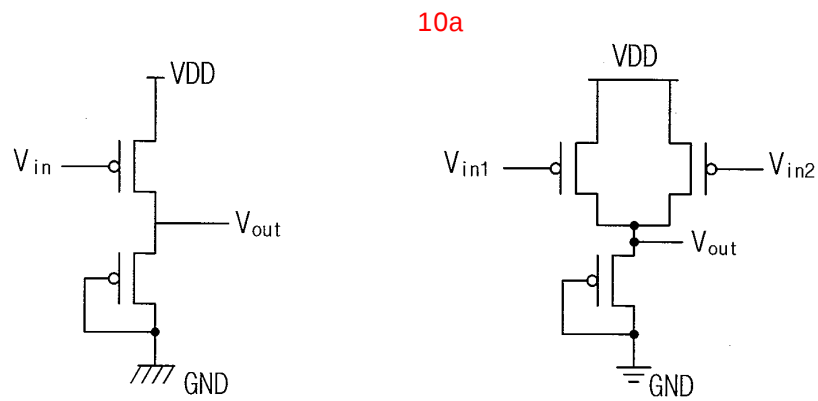
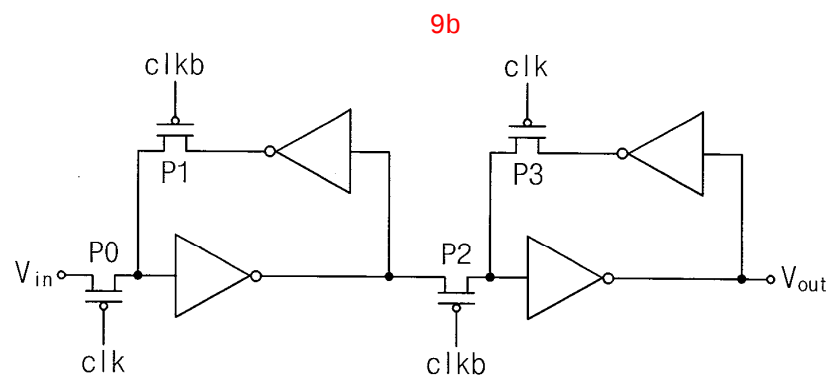
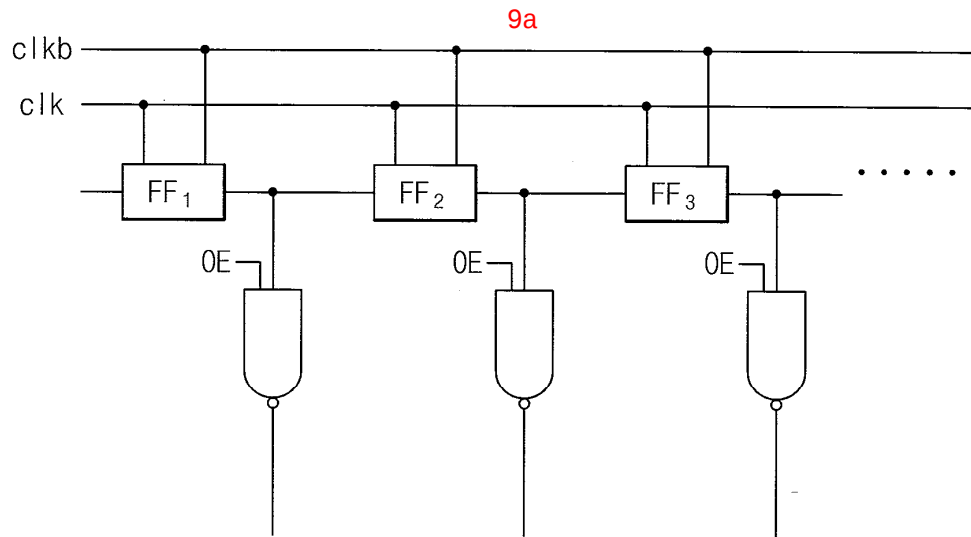
18

1, 4 5 NAND





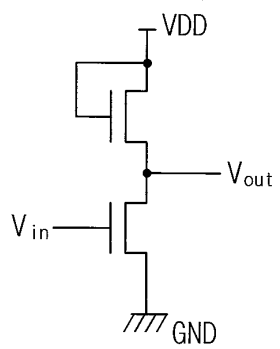




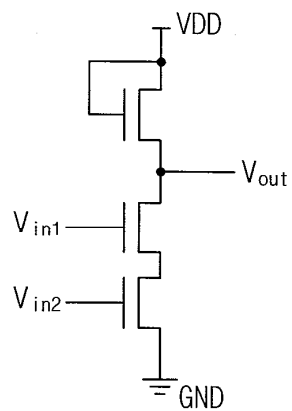
<인버터>

<NAND 게이트>

10b



<인버터>



<NAND 게이트>

专利名称(译)	有机电致发光显示装置，其驱动方法和驱动装置		
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当前申请(专利权)人(译)	三星SD眼有限公司		
[标]发明人	SHIN DONGYONG 신동용 KWON OHKYUNG 권오경		
发明人	신동용 권오경		
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代理人(译)	您是我的专利和法律公司		
其他公开文献	KR100445433B1		
外部链接	Espacenet		

摘要(译)

本发明涉及扫描驱动器的若干部分的扫描驱动器。并且它划分的每个扫描驱动器包括多个触发器，并且多个缓冲器部分具有到相应输入的多个触发器的输出。该触发器由4个NOR门组成。并且缓冲器部分包括NOR门，由反相器组成的OR门，以及PMOS晶体管，缓冲器部分的NOR门和触发器具有清除信号到输入端，包括由2个反相器组成的缓冲器。如果高电平的清除信号输入到在该扫描驱动器中不工作的扫描驱动器，则NOR门的输出总是低电平，并且可以从NOR门的输出端去除形成的静态电流。静态电流，扫描驱动器，有机EL，清晰信号。

